

isc Silicon PNP Power Transistor

2SB1202

DESCRIPTION

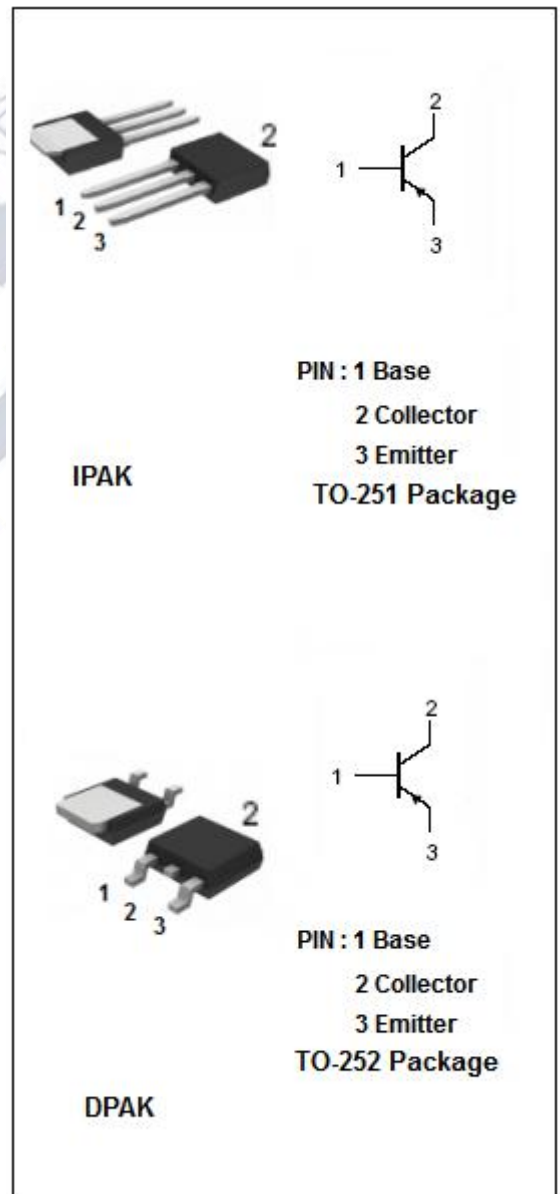
- Large current capacitance and wide ASO
- Small and slim package making it easy to make 2SB1202/2SD1802-used set smaller
- Low collector-to-emitter saturation voltage
- Fast switching speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Voltage regulators, relay drivers, lamp drivers, electrical equipment

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current-Continuous	-3	A
I _{CP}	Collector Current-Pulse	-6	A
P _C	Collector Power Dissipation @ T _C =25°C	15	W
	Collector Power Dissipation @ T _a =25°C	1.0	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon PNP Power Transistor**2SB1202****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2A; I_B = -100mA$			-0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -2A; I_B = -100mA$			-1.2	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu A; I_B = 0$	-60			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1mA; I_B = 0$	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu A; I_C = 0$	-6			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -40V; I_E = 0$			-1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4V; I_C = 0$			-1	μA
h_{FE1}	DC Current Gain	$I_C = -0.1A; V_{CE} = -2V$	100		560	
h_{FE2}	DC Current Gain	$I_C = -3A; V_{CE} = -2V$	35			
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10V; f = 1.0MHz$		39		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -50mA; V_{CE} = -10V$		150		MHz

◆ **h_{FE1} Classifications**

R	S	T	U
100-200	140-280	200-400	280-560

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Outline Drawing

